

# **BUK9226-75A**

# N-channel TrenchMOS logic level FET

Rev. 02 — 27 January 2011

**Product data sheet** 

### 1. Product profile

### 1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

#### 1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

### 1.3 Applications

- 12 V, 24 V and 42 V loads
- Automotive and general purpose power switching
- Motors, lamps and solenoids

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	75	V
$I_D$	drain current	V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	45	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	114	W
Static ch	aracteristics					
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C}$	-	-	29	mΩ
	resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C}$		20.9	24.6	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 13</u> ; see <u>Figure 12</u>	-	22.1	26	mΩ
Avalanci	Avalanche ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D = 49$ A; $V_{sup} \le 75$ V; $R_{GS} = 50$ $\Omega$ ; $V_{GS} = 5$ V; $T_{j(init)} = 25$ °C; unclamped	-	-	120	mJ



# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain	mb	D
3	S	source		
	mounting base; connected to drain	1 3	mbb076 S	
			SOT428 (DPAK)	

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK9226-75A	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

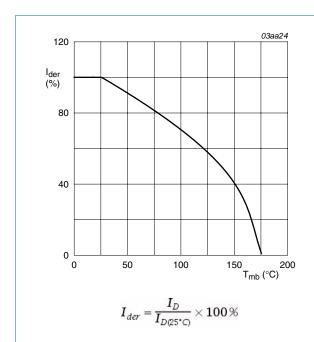
# **Limiting values**

**Limiting values** Table 4.

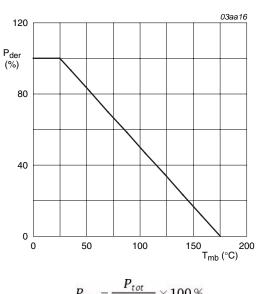
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	75	V
$V_{DGR}$	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	75	V
$V_{GS}$	gate-source voltage		-10	10	V
l <sub>D</sub>	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 5 V; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	45	Α
		$T_{mb} = 100  ^{\circ}C;  V_{GS} = 5  V;  see  \underline{Figure  1}$	-	32	Α
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \mu s$ ; see Figure 3	1 -	182	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	114	W
T <sub>stg</sub>	storage temperature		-55	175	°C
T <sub>j</sub>	junction temperature		-55	175	°C
$V_{GSM}$	peak gate-source voltage	pulsed; t <sub>p</sub> ≤ 50 μs	-15	15	V
Source-drain	diode				
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	-	45	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-	182	Α
Avalanche ru	ggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D = 49 \text{ A}; V_{\text{sup}} \le 75 \text{ V}; R_{\text{GS}} = 50 \Omega;$ $V_{\text{GS}} = 5 \text{ V}; T_{\text{j(init)}} = 25 ^{\circ}\text{C}; \text{ unclamped}$	-	120	mJ

[1] Peak drain current is limited by chip, not package.

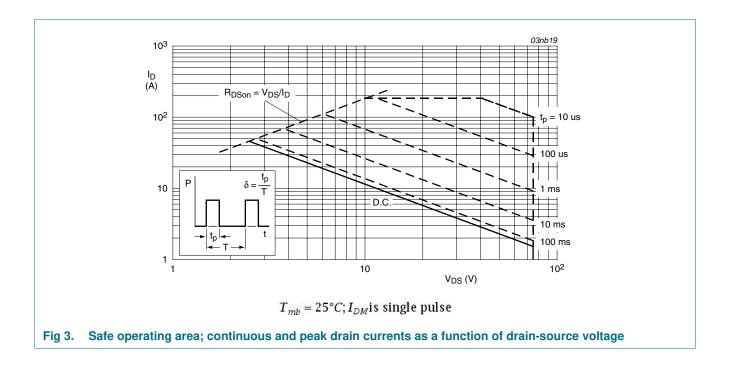


Normalized continuous drain current as a Fig 1. function of mounting base temperature



 $P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$ 

Normalized total power dissipation as a Fig 2. function of mounting base temperature



### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	1.3	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	minimum footprint ; FR4 board	-	71.4	-	K/W

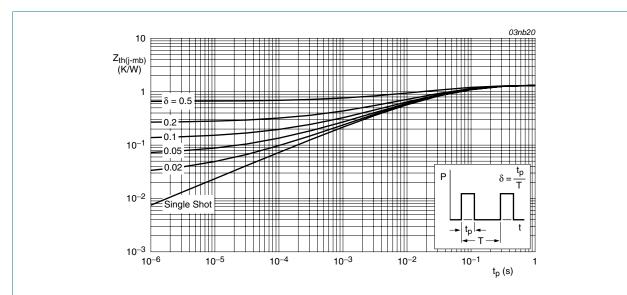


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

### 6. Characteristics

Table 6 Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source breakdown	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	75	-	-	V
	voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	70	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 175$ °C; see Figure 11	0.5	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 25$ °C; see Figure 11	1	1.5	2	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = -55$ °C; see Figure 11	-	-	2.3	V
$I_{DSS}$	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μΑ
	-	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ
		$V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 5 \text{ V}$ ; $I_D = 25 \text{ A}$ ; $T_j = 175 \text{ °C}$ ; see Figure 12; see Figure 13	-	-	54.6	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C}$	-	-	29	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C}$	-	20.9	24.6	mΩ
		$V_{GS} = 5 \text{ V}$ ; $I_D = 25 \text{ A}$ ; $T_j = 25 \text{ °C}$ ; see Figure 13; see Figure 12	-	22.1	26	mΩ
Dynamic	characteristics					
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	2340	3120	рF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 14</u>	-	319	383	рF
C <sub>rss</sub>	reverse transfer capacitance		-	215	295	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 5 \text{ V};$	-	24	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 10 \Omega; T_j = 25 °C$	-	141	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	142	-	ns
t <sub>f</sub>	fall time		-	108	-	ns
L <sub>D</sub>	internal drain inductance	measured from drain lead from package to centre of die ; $T_j = 25$ °C	-	2.5	-	nΗ
L <sub>S</sub>	internal source inductance	measured from source lead from package to source bond pad ; $T_j = 25  ^{\circ}\text{C}$	-	7.5	-	nΗ
Source-d	rain diode					
$V_{SD}$	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 15</u>	-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = 100 \text{ A}/\mu\text{s}; \ V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$	-	49	-	ns
Q <sub>r</sub>	recovered charge	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$ $V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	115	-	nC

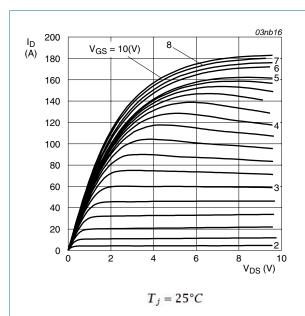


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

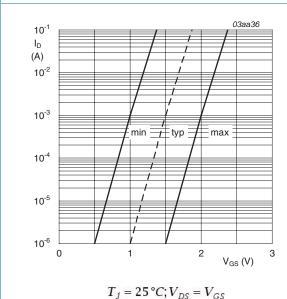
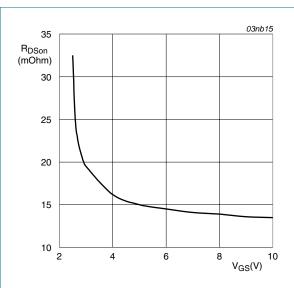


Fig 7. Sub-threshold drain current as a function of gate-source voltage



 $T_j = 25^{\circ}C; I_D = 25A$ 

Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

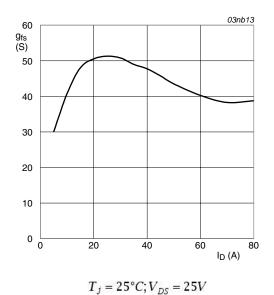


Fig 8. Forward transconductance as a function of drain current; typical values

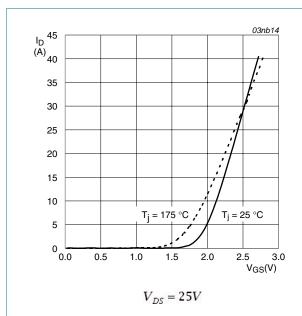


Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

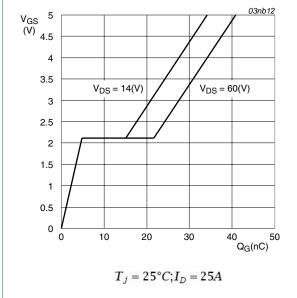


Fig 10. Gate-source voltage as a function of turn-on gate charge; typical values

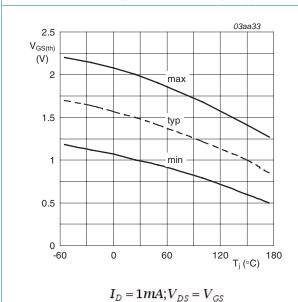


Fig 11. Gate-source threshold voltage as a function of junction temperature

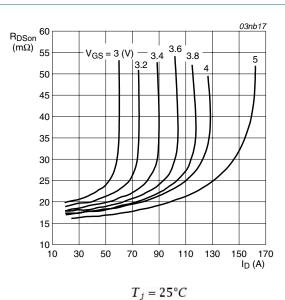


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

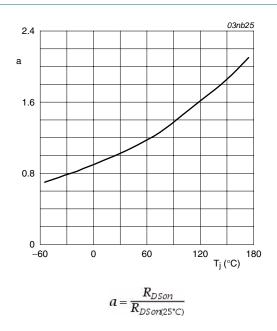


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

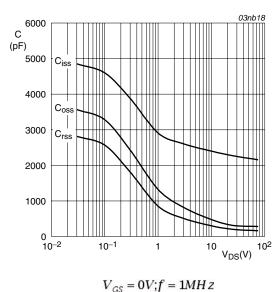


Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

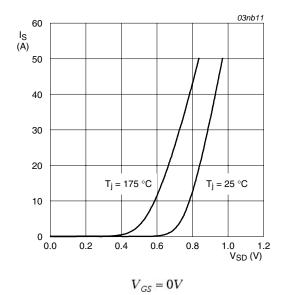


Fig 15. Reverse diode current as a function of reverse diode voltage; typical values

### 7. Package outline

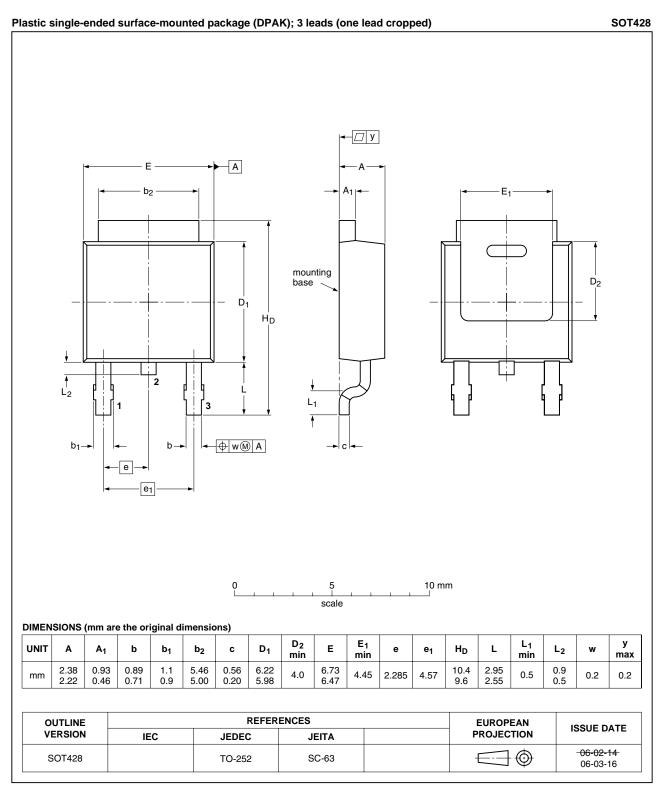


Fig 16. Package outline SOT428 (DPAK)

# 8. Revision history

### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BUK9226-75A v.2	20110127	Product data sheet	-	BUK9226_75A v.1	
Modifications:	<ul> <li>The format of of NXP Semic</li> </ul>		ata sheet has been redesigned to comply with the new identity guideline ctors.		
	<ul> <li>Legal texts ha</li> </ul>	ve been adapted to the new	company name where	appropriate.	
BUK9226_75A v.1	20001010	Product specification	-	-	

### 9. Legal information

#### 9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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# **BUK9226-75A**

### **Nexperia**

N-channel TrenchMOS logic level FET

### 11. Contents

1	Product profile
1.1	General description
1.2	Features and benefits
1.3	Applications
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Limiting values3
5	Thermal characteristics5
6	Characteristics6
7	Package outline
8	Revision history11
9	Legal information12
9.1	Data sheet status
9.2	Definitions12
9.3	Disclaimers
9.4	Trademarks13
10	Contact information 13